I L

F K

I		L	O			
			F	M	F	
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					

H B

	F	I	P	B	I

M M

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

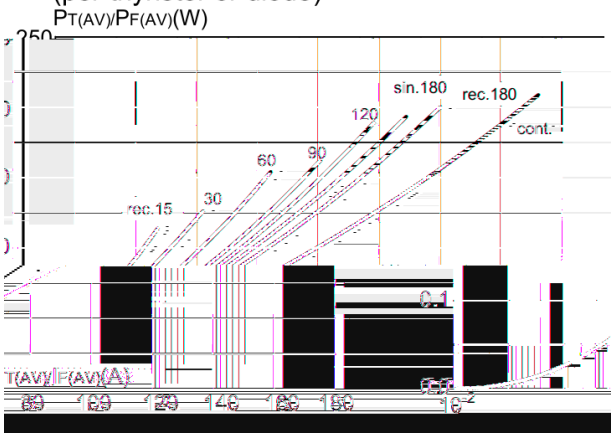

FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

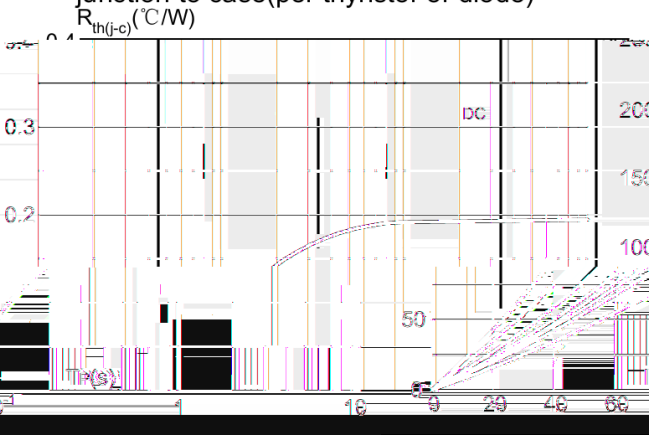

FIG.3: Forward characteristics (per thyristor or diode)

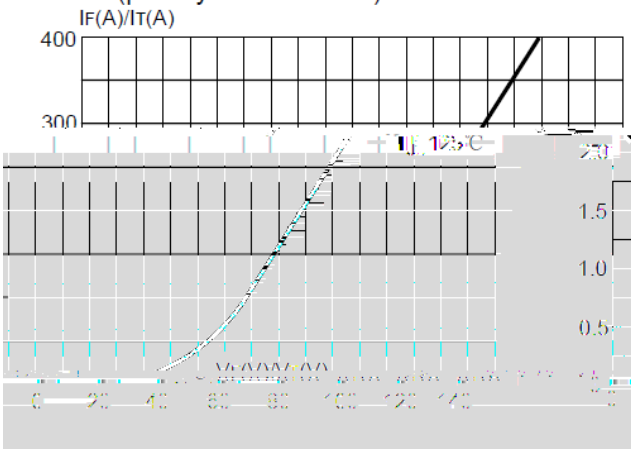

FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

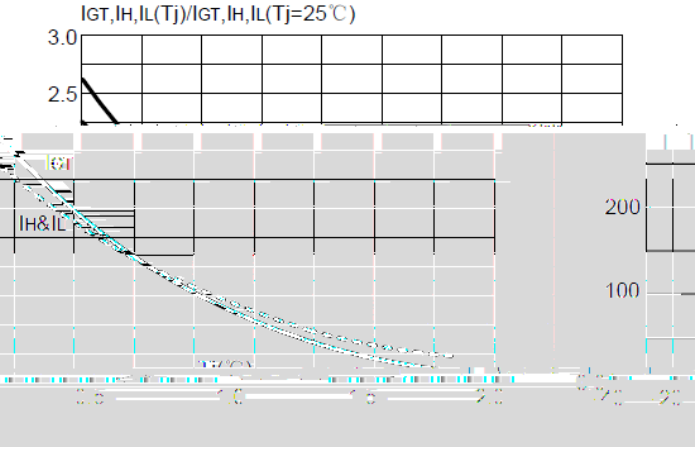

FIG.5 Gate trigger characteristics

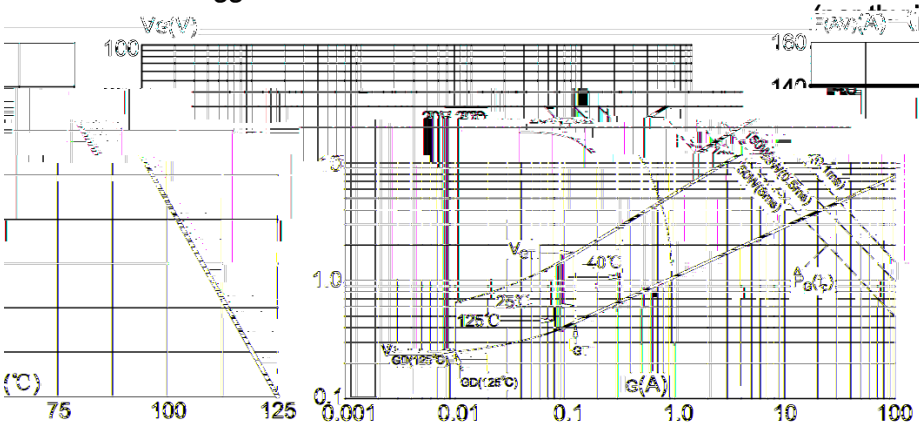
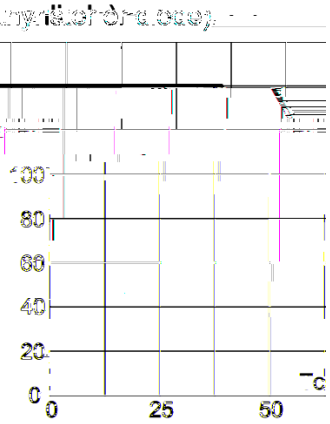
FIG.6: Forward current vs. case temperature